

Features

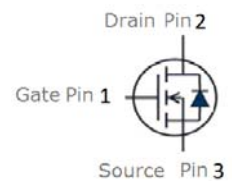
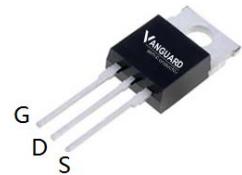
- N-Channel, 10V Logic Level Control
- Enhancement mode
- Very low on-resistance
- Fast Switching
- 100% Avalanche Tested
- Pb-free lead plating; RoHS compliant



Part ID	Package Type	Marking	Tape and reel information
VST018N10HS	TO-220AB	018N10H	50pcs/Tube

V_{DS}	100	V
$R_{DS(on),TYP @ V_{GS}=10V}$	13.8	m Ω
I_D	60	A

TO-220AB



Maximum ratings, at $T_J=25^{\circ}\text{C}$, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		100	V
I_S	Diode continuous forward current	$T_C=25^{\circ}\text{C}$	60	A
I_D	Continuous drain current @ $V_{GS}=10V$	$T_C=25^{\circ}\text{C}$	60	A
		$T_C=100^{\circ}\text{C}$	38	A
I_{DM}	Pulse drain current tested ①	$T_C=25^{\circ}\text{C}$	160	A
EAS	Avalanche energy, single pulsed ②		100	mJ
IAS	Avalanche Current Max	$L=0.5\text{mH}$	34	A
P_D	Maximum power dissipation	$T_C=25^{\circ}\text{C}$	150	W
V_{GS}	Gate-Source voltage		± 20	V
$T_{STG} T_J$	Storage and operating temperature range		-55 to 175	$^{\circ}\text{C}$

Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	1.0	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	42	$^{\circ}\text{C/W}$

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T _c = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	100	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current(T _c =25°C)	V _{DS} =100V,V _{GS} =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T _c =125°C)	V _{DS} =100V,V _{GS} =0V	--	--	100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V,V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} ,I _D =250μA	2.0	3.0	4.0	V
R _{DS(ON)}	Drain-Source On-State Resistance③	V _{GS} =10V, I _D =35A	--	13.8	18	mΩ
Dynamic Electrical Characteristics @ T _c = 25°C (unless otherwise stated)						
R _g	Gate Resistance	V _{DS} =30V,V _{GS} =0V, f=1MHz	--	1.5	--	Ω
C _{iss}	Input Capacitance		--	3380	--	pF
C _{oss}	Output Capacitance		--	195	--	pF
C _{rss}	Reverse Transfer Capacitance		--	165	--	pF
Q _g	Total Gate Charge	V _{DS} =50V,I _D =20A, V _{GS} =10V	--	55	--	nC
Q _{gs}	Gate-Source Charge		--	14	--	nC
Q _{gd}	Gate-Drain Charge		--	17	--	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =50V, I _D =5A, R _G =6.8Ω, V _{GS} =10V	--	24	--	nS
t _r	Turn-on Rise Time		--	19	--	nS
t _{d(off)}	Turn-Off Delay Time		--	35	--	nS
t _f	Turn-Off Fall Time		--	13	--	nS
Source- Drain Diode Characteristics@ T _c = 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage	I _{SD} =35A,V _{GS} =0V	--	0.89	1.2	V
t _{rr}	Reverse Recovery Time	T _j =25°C,I _{sd} =20A, V _{GS} =0V	--	22	--	nS
Q _{rr}	Reverse Recovery Charge	di/dt=500A/μs		93		nC

NOTE:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH, R_G = 25Ω, I_{AS} = 20A, V_{GS} = 10V. Part not recommended for use above this value
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.

Typical Characteristics

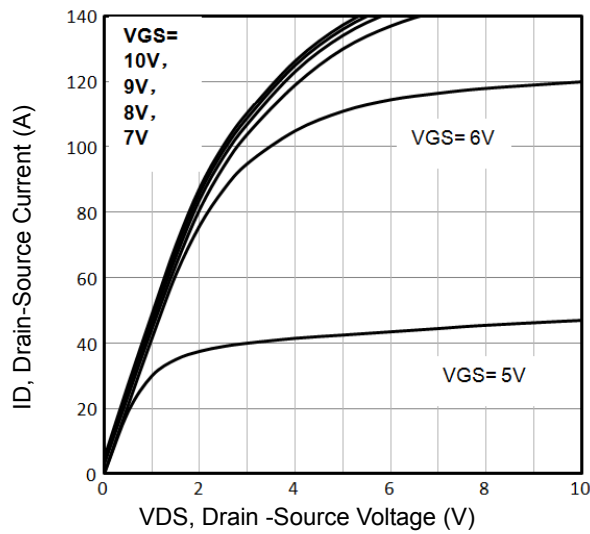


Fig1. Typical Output Characteristics

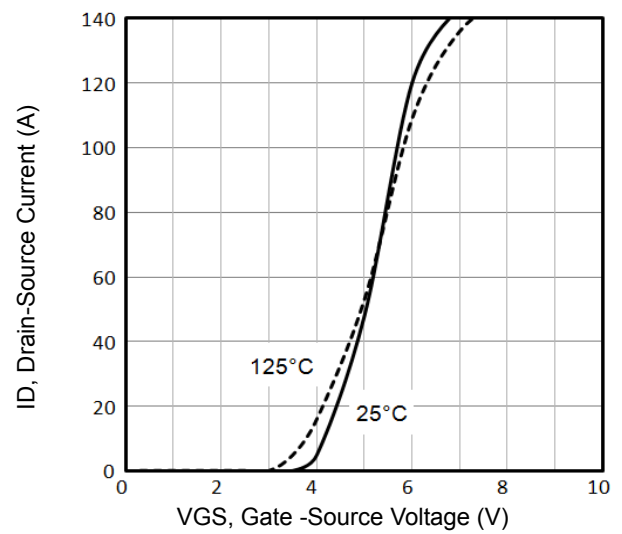


Fig2. Typical Transfer Characteristics

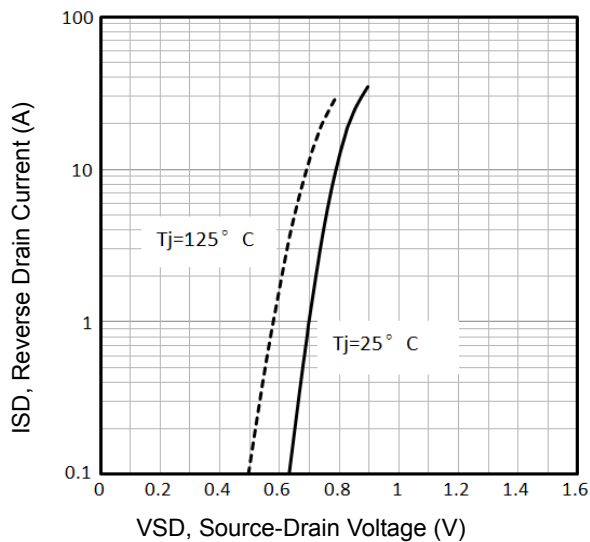


Fig3. Typical Source-Drain Diode Forward Voltage

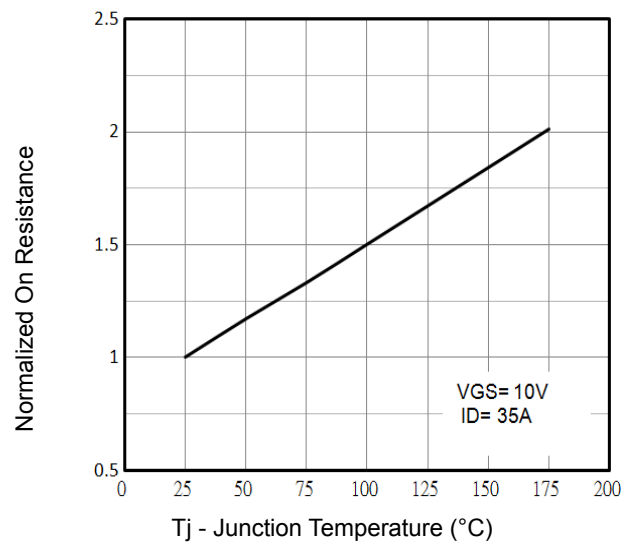


Fig4. Normalized On-Resistance Vs. T_j

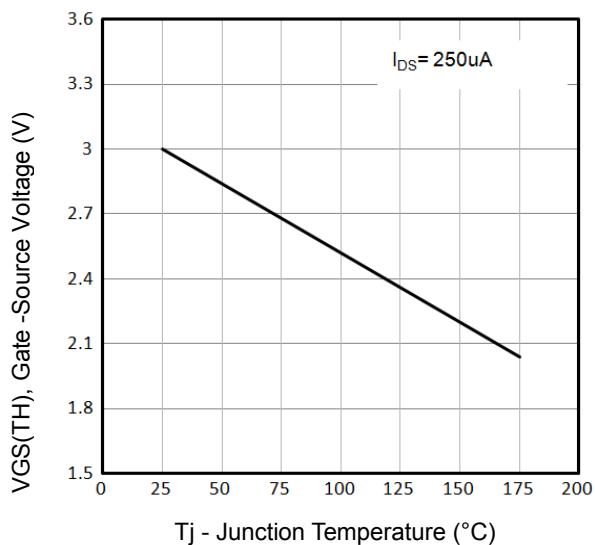


Fig5. $V_{GS(TH)}$ Gate-Source Voltage Vs. T_j

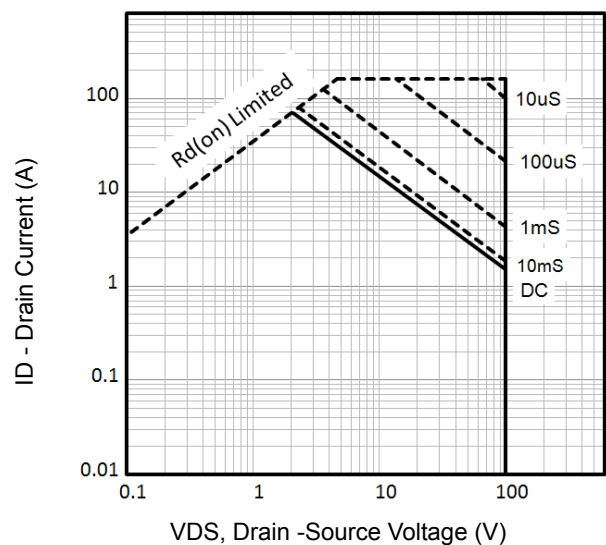
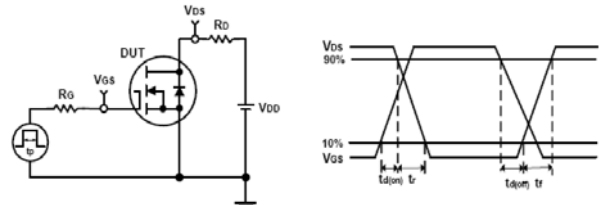
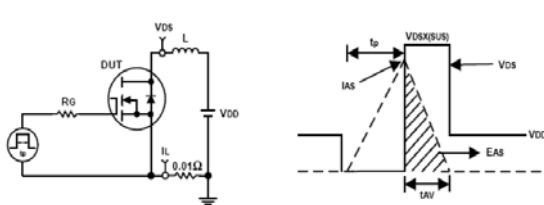
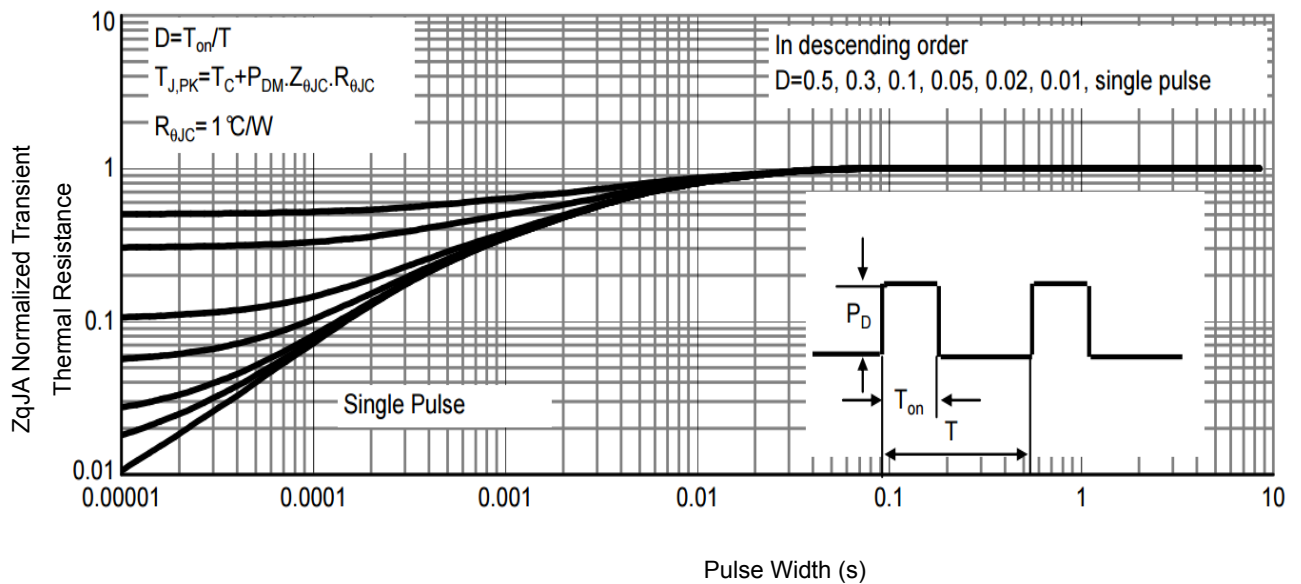
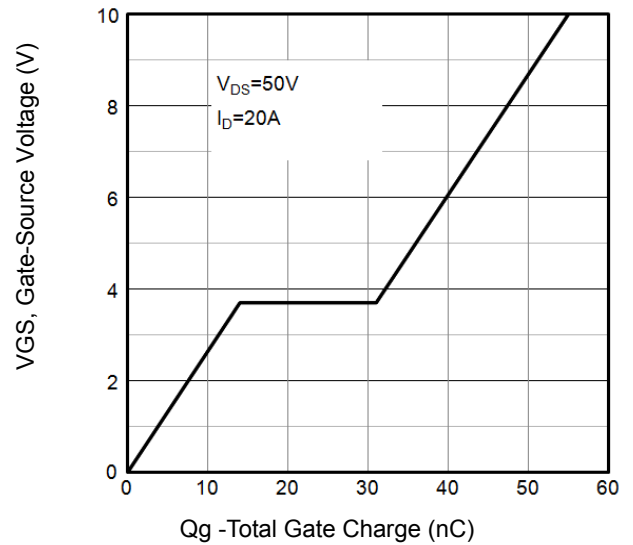
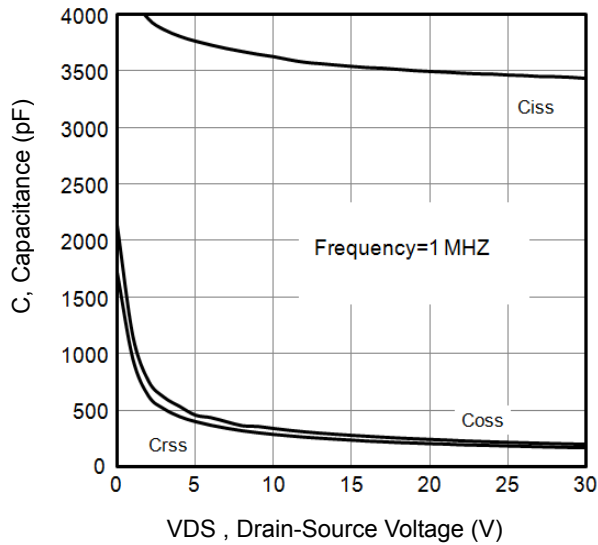
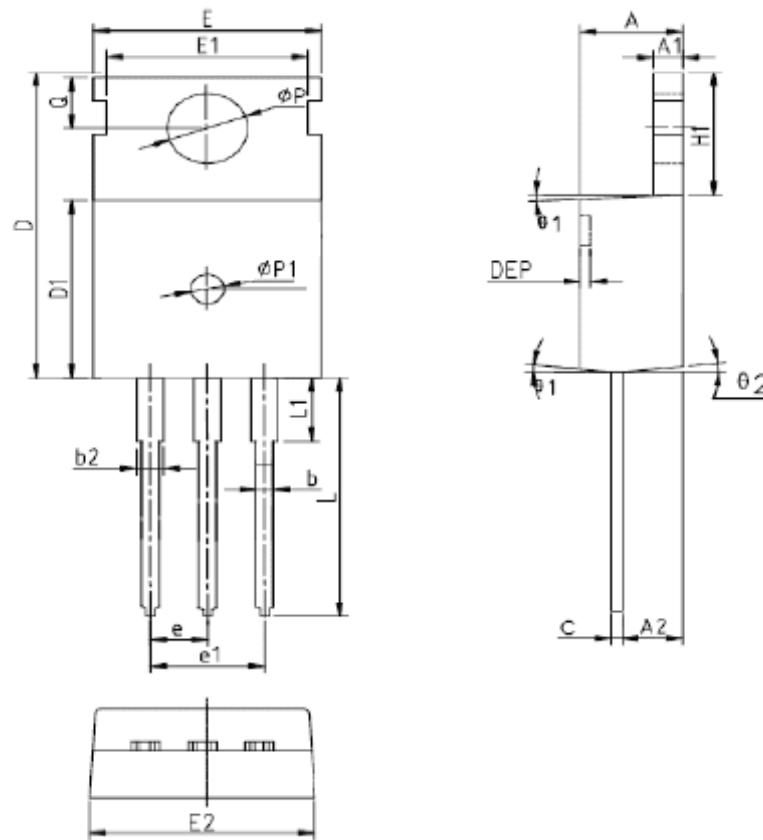


Fig6. Maximum Safe Operating Area

Typical Characteristics



TO-220AB Package Outline



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	θp1	1.40	1.50	1.60	0.055	0.059	0.063
A1	1.27	1.30	1.33	0.050	0.051	0.052	e	2.54BSC			0.1BSC		
A2	2.35	2.40	2.50	0.093	0.094	0.098	e1	5.08BSC			0.2BSC		
b	0.77	-	0.90	0.030	-	0.035	H1	6.40	6.50	6.60	0.252	0.256	0.260
b2	1.23	-	1.36	0.048	-	0.054	L	12.75	-	13.17	0.502	-	0.519
C	0.48	0.50	0.52	0.019	0.020	0.021	L1	-	-	3.95	-	-	0.156
D	15.40	15.60	15.80	0.606	0.614	0.622	L2	2.50REF.			0.098REF.		
D1	9.00	9.10	9.20	0.354	0.358	0.362	θp	3.57	3.60	3.63	0.141	0.142	0.143
DEP	0.05	0.10	0.20	0.002	0.004	0.008	Q	2.73	2.80	2.87	0.107	0.110	0.113
E	9.70	9.90	10.10	0.382	0.389	0.398	θ 1	5°	7°	9°	5°	7°	9°
E1	-	8.70	-	-	0.343	-	θ 2	1°	3°	5°	1°	3°	5°
E2	9.80	10.00	10.20	0.386	0.394	0.401							

Customer Service

Sales and Service:

sales@vgsemi.com

Vanguard Semiconductor CO., LTD

TEL: (86-755) -26902410

FAX: (86-755) -26907027

WEB: www.vgsemi.com